

<b>V<sub>DSS</sub> , 30V</b> <b>R<sub>DS(ON)</sub> , 27mΩ (max.) @ V<sub>GS</sub>=10V</b> <b>R<sub>DS(ON)</sub> , 37mΩ (max.) @ V<sub>GS</sub>=4.5V</b> <b>I<sub>D</sub> , 25A</b>	<b>PDFN 5x6-8L (Dual)</b>		

Description	Features
The SGD30N24QD uses advanced Trench technology and designs to provide excellent R <sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul style="list-style-type: none"> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input/Output Leakage</li> <li>Pb-free lead plating; RoHS compliant</li> </ul>
	<b>Applications</b> <ul style="list-style-type: none"> <li>Motor / Body Load Control</li> <li>Automotive Systems</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>

## Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGD30N24QD	Halogen-Free	PDFN 5x6-8L (Dual)	QD	Tape & Reel	2,500

## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current-Continuous	T <sub>C</sub> =25°C	I <sub>D</sub>	25	A
	T <sub>C</sub> =70°C		20	A
Drain Current-Pulsed <sup>Note 1</sup>		I <sub>DM</sub>	70	A
Maximum Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	31.3	W
	T <sub>A</sub> =25°C		2	W
Operating Junction Temperature Range		T <sub>J</sub> T <sub>STG</sub>	-55 to +150	°C

## Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>Note 2</sup>	R <sub>θJA</sub>	Steady State	-	-	62	°C/W
Maximum Junction-to-Case <sup>Note 2</sup>	R <sub>θJC</sub>	Steady State	-	-	4	°C/W

## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA	1	1.5	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>DS</sub> =6A	-	-	27	mΩ
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =4A	-	-	37	

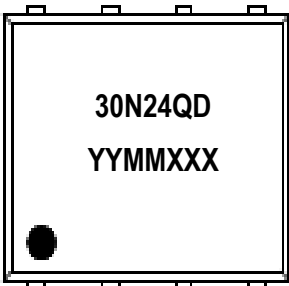
DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	-	407	-	pF
Output Capacitance	C <sub>oss</sub>		-	60	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	50	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =12V, V <sub>GS</sub> =10 V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =6A	-	7.5	-	ns
Rise Time	t <sub>r</sub>		-	45	-	
Turn-Off Delay Time	T <sub>d(off)</sub>		-	10	-	
Fall Time	t <sub>f</sub>		-	3.6	-	
Total Gate Charge at 10V	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>DS</sub> =6A, V <sub>GS</sub> =4.5V	-	4.9	-	nC
Gate to Source Gate Charge	Q <sub>gs</sub>		-	0.9	-	
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	2.4	-	

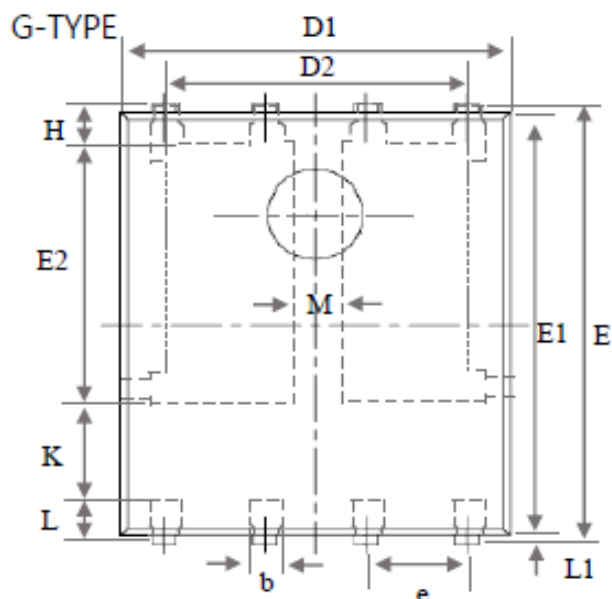
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current <sup>Note 2, 3</sup>	I <sub>S</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	-	-	6	A
Pulsed Source Current <sup>Note 1, 3</sup>	I <sub>SM</sub>		-	-	24	A
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A	-	-	1.2	V

- Notes:**
- Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
  - R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design. R<sub>θJA</sub> shown below for single device operation on FR-4 in still air.
  - The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

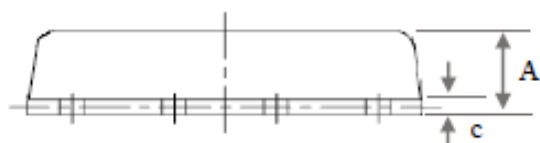
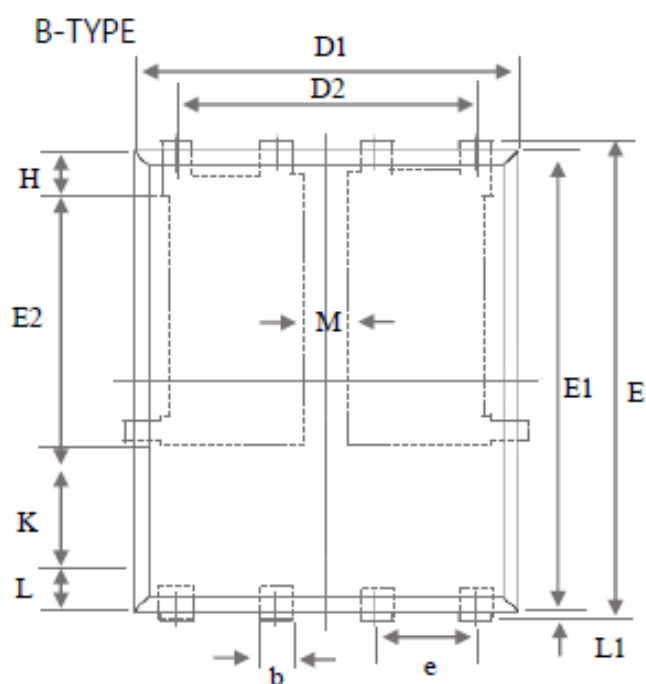
## Marking Information

PDFN 5x6-8L (Dual A) (QD)	Marking Rule
<p>Laser Marking</p>  <p>Diagram</p>	<p><u>Line 1</u> : Device 30N24QD</p> <p><u>Line 2</u> : Date Code YYMMXXX</p> <p>YY : Year Code MM : Month Code XXX : Serial Number</p>

## Package of Dimension



Symbol	Min	Nor	Max
A	0.90	1.04	1.17
b	0.33	0.42	0.51
c	0.203 BSC		
D1	4.80	4.90	5.00
D2	3.61	3.96	4.30
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e	1.27 BSC		
H	0.38	0.50	0.61
K	1.10	-	-
L	0.38	0.56	0.74
L1	0.50	0.38	0.25
M	0.50	-	-

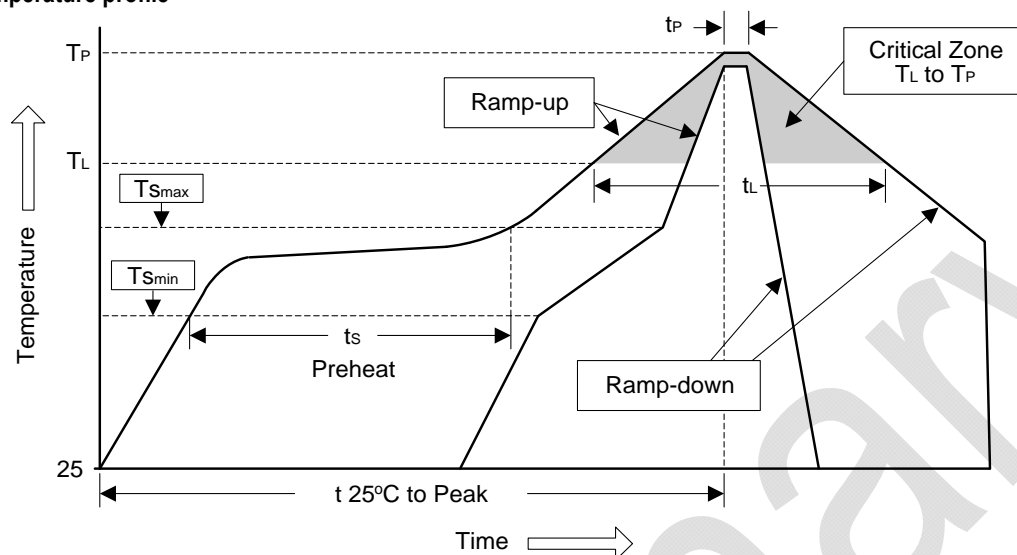


1. All dimension are in millimeters.
2. Dimension does not include burrs and mold flash/protrusions.

## Soldering Methods for Silicongear's Products

- Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (TL to TP)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (TSmin)	100°C	150°C
- Temperature Max (TSmax)	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
TSmax to TL		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (TL)	183°C	217°C
- Time (tL)	60 to 150 sec	60 to 150 sec
Peak Temperature (TP)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (tP)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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